

### Wideband, Low-Distortion Fully Differential Amplifiers

Check for Samples: THS4502, THS4503

#### **FEATURES**

Fully Differential Architecture

Bandwidth: 370 MHz
Slew Rate: 2800 V/µs
IMD<sub>3</sub>: -95 dBc at 30 MHz
OIP<sub>3</sub>: 51 dBm at 30 MHz

Output Common-Mode Control

 Wide Power Supply Voltage Range: 5 V, ±5 V, 12 V. 15 V

Centered Input Common-Mode Range

Power-Down Capability (THS4502)

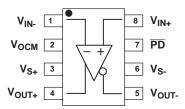
Evaluation Module Available

#### **APPLICATIONS**

- High Linearity Analog-to-Digital Converter Preamplifier
- Wireless Communication Receiver Chains
- Single-Ended to Differential Conversion
- Differential Line Driver
- · Active Filtering of Differential Signals

#### DESCRIPTION

The THS4502 and THS4503 are high-performance fully differential amplifiers from Texas Instruments. The THS4502, featuring power-down capability, and the THS4503, without power-down capability, set new performance standards for fully differential amplifiers with unsurpassed linearity, supporting 14-bit operation through 40 MHz. Package options include the 8-pin SOIC and the 8-pin MSOP with PowerPAD $^{\rm TM}$  for a smaller footprint, enhanced ac performance, and improved thermal dissipation capability.



#### **RELATED DEVICES**

DEVICE <sup>(1)</sup>	DESCRIPTION
THS4500/1	370 MHz, 2800 V/µs, V <sub>ICR</sub> Includes V <sub>S</sub> _
THS4502/3	370 MHz, 2800 V/µs, Centered V <sub>ICR</sub>
THS4120/1	3.3 V, 100 MHz, 43 V/µs, 3.7 nV√Hz
THS4130/1	±15 V, 150 MHz, 51 V/µs, 1.3 nV√Hz
THS4140/1	±15 V, 160 MHz, 450 V/µs, 6.5 nV√Hz
THS4150/1	±15 V, 150 MHz, 650 V/µs, 7.6 nV√Hz

(1) Even numbered devices feature power-down capability.

#### WARNING

The THS4502 and THS4503 may have low-level oscillation when the die temperature (also known as the junction temperature) exceeds +60°C. These devices are not recommended for new designs where the die temperature is expected to exceed +60°C. For more information, see Maximum Die Temperature to Prevent Oscillation section.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PowerPAD is a trademark of Texas Instruments.

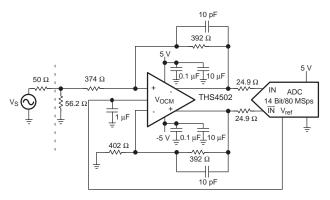


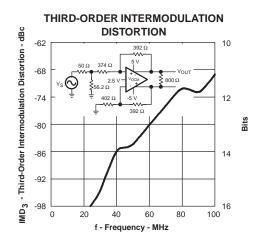


This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### **APPLICATION CIRCUIT DIAGRAM**



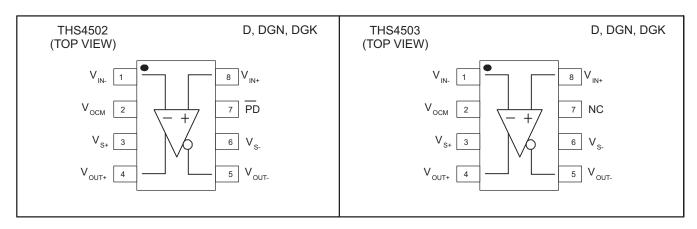


#### **PACKAGE/ORDERING INFORMATION**

		ORDERABLE PACKAGE AND NUMBER						
TEMPERATURE	PLASTIC SMALL OUTLINE	PLASTIC MSOP <sup>(1)</sup> PowerPAD		PLASTIC	MSOP			
	(D)	(DGN)	SYMBOL	(DGK)	SYMBOL			
0°C to 70°C	THS4502CD	THS4502CDGN	BCG	THS4502CDGK	ATX			
0 0 10 70 0	THS4503CD	THS4503CDGN	BCK	THS4503CDGK	ATY			
40°C to 05°C	THS4502ID	THS4502IDGN	BCI	THS4502IDGK	ASX			
-40°C to 85°C	THS4503ID	THS4503IDGN	BCL	THS4503IDGK	ASY			

 All packages are available taped and reeled. The R suffix standard quatity is 2500. The T suffix standard quantity is 250 (e.g., THS4502DT).

#### **PIN ASSIGNMENTS**





#### **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range unless otherwise noted (1)

		UNIT
Supply voltage, V <sub>S</sub>		16.5 V
Input voltage, V <sub>I</sub>		±V <sub>S</sub>
Output current, IO (2)		150 mA
Differential input voltage, V <sub>ID</sub>		4 V
Continuous power dissipation		See Dissipation Rating Table
Maximum junction temperature, T <sub>J</sub> <sup>(3)</sup>		150°C
Maximum junction temperature, continuous ope	eration, long term reliability, T <sub>J</sub> <sup>(4)</sup>	125°C
Maximum junction temperature to prevent oscil	lation, T <sub>J</sub> <sup>(5)</sup>	60°C
Operating free cir temperature range T	C suffix	0°C to 70°C
Operating free-air temperature range, T <sub>A</sub>	I suffix	-40°C to 85°C
Storage temperature range, T <sub>stg</sub>		-65°C to 150°C

- (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
- (2) The THS450x may incorporate a PowerPAD on the underside of the chip. This acts as a heatsink and must be connected to a thermally dissipative plane for proper power dissipation. Failure to do so may result in exceeding the maximum junction temperature which could permanently damage the device. See TI technical brief SLMA002 for more information about utilizing the PowerPAD thermally enhanced package.
- (3) The absolute maximum temperature under any condition is limited by the constraints of the silicon process.
- (4) The maximum junction temperature for continuous operation is limited by package constraints. Operation above this temperature may result in reduced reliability and/or lifetime of the device.
- (5) See Maximum Die Temperature to Prevent Oscillation section in the Application Information of this data sheet.

#### PACKAGE DISSIPATION RATINGS

PACKAGE	θ <sub>JC</sub> (° <b>C/W</b> )	θ <sub>JA</sub> <sup>(1)</sup> (° <b>C/W)</b>					
D (8 pin)	38.3	97.5					
DGN (8 pin)	4.7	58.4					
DGK (8 pin)	54.2	260					

<sup>(1)</sup> This data was taken using the JEDEC standard High-K test PCB.

#### RECOMMENDED OPERATING CONDITIONS

		MIN	NOM	MAX	UNIT
Cumply valtage	Dual supply		±5	±7.5	W
Supply voltage	Single supply	4.5	5	15	V
On another from a six to remove the T	C suffix	0		70	°C
Operating free- air temperature, T <sub>A</sub>	I suffix	-40		85	C



### ELECTRICAL CHARACTERISTICS $V_S = \pm 5 V$

 $R_f = R_g = 499\Omega$ ,  $R_L = 800 \Omega$ , G = +1, Single-ended input unless otherwise noted.

			THS4502 AND THS4503				
PARAMETER	TEST CONDITIONS	TYP	OVER TEMPERATURE <sup>(1)</sup>				MIN/
	TEST CONDITIONS	25°C	25°C	0°C to 70°C	-40°C to 85°C	UNITS	TYP/ MAX
AC PERFORMANCE							
	$G = +1$ , $P_{IN} = -20$ dBm, $R_f = 392$ Ω	370				MHz	Тур
Cmall aignal bandwidth	$G = +2$ , $P_{IN} = -30$ dBm, $R_f = 1$ k $\Omega$	175				MHz	Тур
Small-signal bandwidth	$G = +5$ , $P_{IN} = -30$ dBm, $R_f = 1.3$ kΩ	70				MHz	Тур
	$G = +10$ , $P_{IN} = -30$ dBm, $R_f = 1.3 \text{ k}\Omega$	30				MHz	Тур
Gain-bandwidth product	G > +10	300				MHz	Тур
Bandwidth for 0.1 dB flatness	P <sub>IN</sub> = -20 dBm	150				MHz	Тур
Large-signal bandwidth	V <sub>P</sub> = 2 V	220				MHz	Тур
Slew rate	4 V <sub>PP</sub> Step	2800				V/µs	Тур
Rise time	2 V <sub>PP</sub> Step	0.8				ns	Тур
Fall time	2 V <sub>PP</sub> Step	0.6				ns	Тур
Settling time to 0.01%	$V_O = 4 V_{PP}$	8.3				ns	Тур
Settling time to 0.1%	$V_O = 4 V_{PP}$	6.3				ns	Тур
Harmonic distortion	G = +1, V <sub>O</sub> = 2 V <sub>PP</sub>						Тур
and .	f = 8 MHz	-83				dBc	Тур
2 <sup>nd</sup> harmonic	f = 30 MHz	-74				dBc	Тур
	f = 8 MHz	-97				dBc	Тур
3 <sup>rd</sup> harmonic	f = 30 MHz	-78				dBc	Тур
Third-order intermodulation distortion	$V_O = 2V_{PP}$ , $f_c$ = 30 MHz, $R_f$ = 392 $\Omega$ , 200 kHz tone spacing	-94				dBc	Тур
Third-order output intercept point	$f_c$ = 30 MHz, $R_f$ = 392 Ω, Referenced to 50 Ω	52				dBm	Тур
Input voltage noise	f > 1 MHz	6.8				nV/√ <del>Hz</del>	Тур
Input current noise	f > 100 kHz	1.7				pA/√Hz	Тур
Overdrive recovery time	Overdrive = 5.5 V	75				ns	Тур
DC PERFORMANCE							
Open-loop voltage gain		55	52	50	50	dB	Min
Input offset voltage		-1	-4/+2	-5/+3	-6/+4	mV	Max
Average offset voltage drift				±10	±10	μV/°C	Тур
Input bias current		4	4.6	5	5.2	μΑ	Max
Average bias current drift				±10	±10	nA/°C	Тур
Input offset current		0.5	1	2	2	μA	Max
Average offset current drift				±40	±40	nA/°C	Тур
INPUT		1		1.		ı	
Common-mode input range		±4.0	±3.7	±3.4	±3.4	V	Min
Common-mode rejection ratio		80	74	70	70	dB	Min
Input impedance		10 <sup>7</sup>    1				Ω    pF	Тур
OUTPUT	-			<u>I</u>	1		
Differential output voltage swing	$R_L = 1 \text{ k}\Omega$	±8	±7.6	±7.4	±7.4	V	Min
Differential output current drive	$R_1 = 20\Omega$	120	110	100	100	mA	Min
Output balance error	P <sub>IN</sub> = -20 dBm, f = 100 kHz	-58				dB	Тур
Closed-loop output impedance (single-ended)	f = 1 MHz	0.1				Ω	Тур

<sup>(1)</sup> See Maximum Die Temperature to Prevent Oscillation section in the Application Information of this data sheet.



### ELECTRICAL CHARACTERISTICS $V_s = \pm 5 V$ (continued)

 $R_f = R_g = 499\Omega$ ,  $R_L = 800 \Omega$ , G = +1, Single-ended input unless otherwise noted.

			THS4502 AND THS4503				
PARAMETER	TEST CONDITIONS	TYP	0	VER TEMPE	RATURE <sup>(1</sup>	)	MIN/
TAKAMETEK	1201 GONDINGNO	25°C	25°C	0°C to 70°C	-40°C to 85°C	UNITS	TYP/ MAX
OUTPUT COMMON-MODE VOLTAGE	E CONTROL						
Small-signal bandwidth	$R_L = 400\Omega$	180				MHz	Тур
Slew rate	2 V <sub>PP</sub> step	87				V/µs	Тур
Minimum gain		1	0.98	0.98	0.98	V/V	Min
Maximum gain		1	1.02	1.02	1.02	V/V	Max
Common-mode offset voltage		+2	-1.6/+6.8	-3.6/+8.8	-4.6/+9.8	mV	Max
Input bias current	V <sub>OCM</sub> = 2.5 V	100	150	170	170	μΑ	Max
Input voltage range		±4	±3.7	±3.4	±3.4	V	Min
Input impedance		25    1				kΩ    pF	Тур
Maximum default voltage	V <sub>OCM</sub> left floating	0	0.05	0.10	0.10	V	Max
Minimum default voltage	V <sub>OCM</sub> left floating	0	-0.05	-0.10	-0.10	V	Min
POWER SUPPLY							
Specified operating voltage		±5	±8.25	±8.25	±8.25	V	Max
Maximum quiescent current		23	28	32	34	mA	Max
Minimum quiescent current		23	18	14	12	mA	Min
Power supply rejection (±PSRR)		80	76	73	70	dB	Min
POWER DOWN (THS4502 ONLY)							
Enable voltage threshold	Device enabled ON above -2.9 V		-2.9			V	Min
Disable voltage threshold	Device disabled OFF below -4.3 V		-4.3			V	Max
Power-down quiescent current		800	1000	1200	1200	μΑ	Max
Input bias current		200	240	260	260	μΑ	Max
Input impedance		50    1				kΩ    pF	Тур
Turnon time delay		1000				ns	Тур
Turnoff time delay		800				ns	Тур

#### **ELECTRICAL CHARACTERISTICS V<sub>s</sub> = 5 V**

 $R_f = R_g = 499 \Omega$ ,  $R_L = 800 \Omega$ , G = +1, Single-ended input unless otherwise noted.

			THS4502 AND THS4503					
PARAMETER	TEST CONDITIONS	TYP 25°C 25°	C	OVER TEMPERATURE <sup>(1)</sup>				
	TEST CONDITIONS		25°C	0°C to 70°C	-40°C to 85°C	UNITS	YP/M AX	
AC PERFORMANCE								
	$G = +1, P_{IN} = -20 \text{ dBm}, R_f = 392 \Omega$	320				MHz	Тур	
Concil aignal handwidth	$G = +2$ , $P_{IN} = -30$ dBm, $R_f = 1$ k $\Omega$	160				MHz	Тур	
Small-signal bandwidth	$G = +5$ , $P_{IN} = -30$ dBm, $R_f = 1.3$ k $\Omega$	60				MHz	Тур	
	$G = +10$ , $P_{IN} = -30$ dBm, $R_f = 1.3$ kΩ	30				MHz	Тур	
Gain-bandwidth product	G > +10	300				MHz	Тур	
Bandwidth for 0.1 dB flatness	P <sub>IN</sub> = -20 dBm	180				MHz	Тур	
Large-signal bandwidth	V <sub>P</sub> = 1 V	200				MHz	Тур	
Slew rate	2 V <sub>PP</sub> Step	1300				V/µs	Тур	
Rise time	2 V <sub>PP</sub> Step	0.6				ns	Тур	
Fall time	2 V <sub>PP</sub> Step	0.8				ns	Тур	
Settling time to 0.01%	V <sub>O</sub> = 2 V Step	13.1				ns	Тур	

<sup>(1)</sup> See Maximum Die Temperature to Prevent Oscillation section in the Application Information of this data sheet.



### **ELECTRICAL CHARACTERISTICS V<sub>S</sub> = 5 V (continued)**

 $R_f = R_g = 499 \ \Omega$ ,  $R_L = 800 \ \Omega$ , G = +1, Single-ended input unless otherwise noted.

			Т	HS4502 AN	ID THS4503	3	
PARAMETER	TEST CONDITIONS	TYP	OVER TEMPERATURE <sup>(1)</sup>				MIN/T
TANAMETEN		25°C	25°C	0°C to 70°C	-40°C to 85°C	UNITS	YP/M AX
Settling time to 0.1%	V <sub>O</sub> = 2 V Step	8.3				ns	Тур
Harmonic distortion	$V_O = 2 V_{PP}$						Тур
2 <sup>nd</sup> harmonic	f = 8 MHz,	-81				dBc	Тур
2 <sup>nd</sup> narmonic	f = 30 MHz	-60				dBc	Тур
3 <sup>rd</sup> harmonic	f = 8 MHz	-74				dBc	Тур
3 · Harmonic	f = 30 MHz	-62				dBc	Тур
Input voltage noise	f > 1 MHz	6.8				nV/√ <del>Hz</del>	Тур
Input current noise	f > 100 kHz	1.6				pA/√Hz	Тур
Overdrive recovery time	Overdrive = 5.5 V	75				ns	Тур
DC PERFORMANCE							
Open-loop voltage gain		54	51	49	49	dB	Min
Input offset voltage		-0.6	-3.6/+2.4	-4.6/+3.4	-5.6/+4.4	mV	Max
Average offset voltage drift				±10	±10	μV/°C	Тур
Input bias current		4	4.6	5	5.2	μΑ	Max
Average bias current drift				±10	±10	nA/°C	Тур
Input offset current		0.5	0.7	1.2	1.2	μΑ	Max
Average offset current drift				±20	±20	nA/°C	Тур
INPUT			1		ı		1
Common-mode input range		1 / 4	1.3 / 3.7	1.6 / 3.4	1.6 / 3.4	V	Min
Common-mode rejection ratio		80	74	70	70	dB	Min
Input Impedance		10 <sup>7</sup>    1				Ω    pF	Тур
OUTPUT			ı		ı		1
Differential output voltage swing	$R_L = 1 \text{ k}\Omega$ , Referenced to 2.5 V	±3.3	±2.8	±2.6	±2.6	V	Min
Output current drive	$R_L = 20\Omega$	100	90	80	80	mA	Min
Output balance error	P <sub>IN</sub> = -20 dBm, f = 100 kHz	-58				dB	Тур
Closed-loop output impedance (single-ended)	f = 1 MHz	0.1				Ω	Тур
OUTPUT COMMON-MODE VOLTA	GE CONTROL						
Small-signal bandwidth	$R_L = 400 \Omega$	180				MHz	Тур
Slew rate	2 V <sub>PP</sub> Step	80				V/µs	Тур
Minimum gain		1	0.98	0.98	0.98	V/V	Min
Maximum gain		1	1.02	1.02	1.02	V/V	Max
Common-mode offset voltage		2	-2.2/6.2	-4.2/8.2	-5.2/9.2	mV	Max
Input bias current	V <sub>OCM</sub> = 2.5 V	1	2	3	3	μA	Max
Input voltage range		1/4	1.2/3.8	1.3/3.7	1.3/3.7	V	Min
Input impedance		25    1				kΩ    pF	Тур
Maximum default voltage	V <sub>OCM</sub> left floating	2.5	2.55	2.6	2.6	V	Max
Minimum default voltage	V <sub>OCM</sub> left floating	2.5	2.45	2.4	2.4	V	Min
POWER SUPPLY			1	T	ı	T	
Specified operating voltage		5	16.5	16.5	16.5	V	Max
Maximum quiescent current		20	25	29	31	mA	Max
Minimum quiescent current		20	16	12	10	mA	Min
Power supply rejection (+PSRR)		75	72	69	66	dB	Min



### ELECTRICAL CHARACTERISTICS $V_S = 5 V$ (continued)

 $R_f = R_g = 499 \ \Omega$ ,  $R_L = 800 \ \Omega$ , G = +1, Single-ended input unless otherwise noted.

			7	ND THS4503	3		
PARAMETER	TEST CONDITIONS	TYP	(	OVER TEM	MIN/T		
I ANAMETER	TEST CONDITIONS	25°C	25°C	0°C to 70°C	-40°C to 85°C	UNITS	YP/M AX
POWER DOWN (THS4502 ONLY)							
Enable voltage threshold	Device enabled <i>ON</i> above 2.1 V		2.1			V	Min
Disable voltage threshold	Device disabled <i>OFF</i> below 0.7 V		0.7			V	Max
Power-down quiescent current		600	800	1200	1200	μΑ	Max
Input bias current		100	125	140	140	μΑ	Max
Input impedance		50    1				kΩ    pF	Тур
Turnon time delay		1000				ns	Тур
Turnoff time delay		800				ns	Тур



#### **TYPICAL CHARACTERISTICS**

### Table of Graphs (±5 V)

	FIGURE
Small signal unity gain frequency response	1
Small signal frequency response	2
0.1 dB gain flatness frequency response	3
Harmonic distortion (single-ended input to differential output) vs Frequency	4, 6, 12, 14
Harmonic distortion (differential input to differential output) vs Frequency	5, 7, 13, 15
Harmonic distortion (single-ended input to differential output) vs Output voltage swing	8, 10, 16, 18
Harmonic distortion (differential input to differential output) vs Output voltage swing	9, 11, 17, 19
Harmonic distortion (single-ended input to differential output) vs Load resistance	20
Harmonic distortion (differential input to differential output) vs Load resistance	21
Third order intermodulation distortion (single-ended input to differential output) vs Frequency	22
Third order output intercept point vs Frequency	23
Slew rate vs Differential output voltage step	24
Settling time	25, 26
Large-signal transient response	27
Small-signal transient response	28
Overdrive recovery	29, 30
Voltage and current noise vs Frequency	31
Rejection ratios vs Frequency	32
Rejection ratios vs Case temperature	33
Output balance error vs Frequency	34
Open-loop gain and phase vs Frequency	35
Open-loop gain vs Case temperature	36
Input bias and offset current vs Case temperature	37
Quiescent current vs Supply voltage	38
Input offset voltage vs Case temperature	39
Common-mode rejection ratio vs Input common-mode range	40
Differential output current drive vs Case temperature	41
Harmonic distortion (single-ended and differential input to differential output) vs Output common-mode voltage	42
Small signal frequency response at V <sub>OCM</sub>	43
Output offset voltage at V <sub>OCM</sub> vs Output common-mode voltage	44
Quiescent current vs Power-down voltage	45
Turnon and turnoff delay times	46
Single-ended output impedance in power down vs Frequency	47
Power-down quiescent current vs Case temperature	48
Power-down quiescent current vs Supply voltage	49



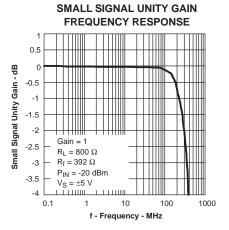
### Table of Graphs (5 V)

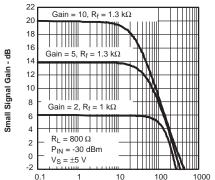
	FIGURE
Small signal unity gain frequency response	50
Small signal frequency response	51
0.1 dB gain flatness frequency response	52
Harmonic distortion (single-ended input to differential output) vs Frequency	53, 54, 61, 63
Harmonic distortion (differential input to differential output) vs Frequency	55, 56, 62, 64
Harmonic distortion (single-ended input to differential output) vs Output voltage swing	57, 58, 65, 67
Harmonic distortion (differential input to differential output) vs Output voltage swing	59, 60, 66, 68
Harmonic distortion (single-ended input to differential output) vs Load resistance	69
Harmonic distortion (differential input to differential output) vs Load resistance	70
Slew rate vs Differential output voltage step	71
Large-signal transient response	72
Small-signal transient response	73
Voltage and current noise vs Frequency	74
Rejection ratios vs Frequency	75
Rejection ratios vs Case temperature	76
Output balance error vs Frequency	77
Open-loop gain and phase vs Frequency	78
Open-loop gain vs Case temperature	79
Input bias and offset current vs Case temperature	80
Quiescent current vs Supply voltage	81
Input offset voltage vs Case temperature	82
Common-mode rejection ratio vs Input common-mode range	83
Output drive vs Case temperature	84
Harmonic distortion (single-ended and differential input) vs Output common-mode range	85
Small signal frequency response at V <sub>OCM</sub>	86
Output offset voltage vs Output common-mode voltage	87
Quiescent current vs Power-down voltage	88
Turnon and turnoff delay times	89
Single-ended output impedance in power down vs Frequency	90
Power-down quiescent current vs Case temperature	91
Power-down quiescent current vs Supply voltage	92

Product Folder Link(s): THS4502 THS4503



### TYPICAL CHARACTERISTICS (±5 V Graphs) AIN SMALL SIGNAL FREQUENCY RESPONSE





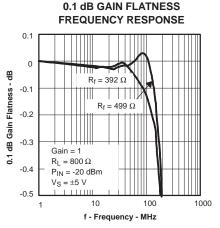


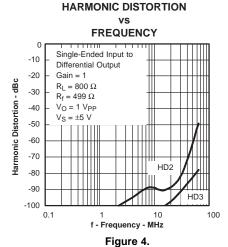
Figure 1.

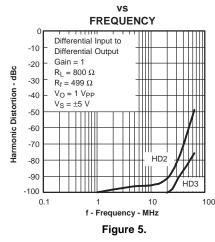
Figure 2.

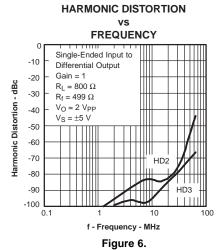
HARMONIC DISTORTION

f - Frequency - MHz

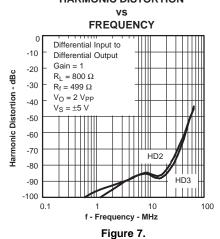
Figure 3.

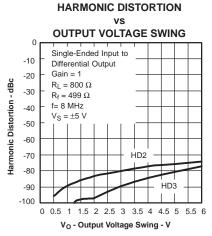


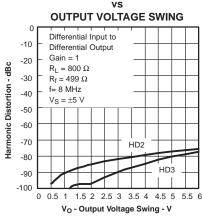




HARMONIC DISTORTION







HARMONIC DISTORTION

Figure 8.

Figure 9.



# TYPICAL CHARACTERISTICS (±5 V Graphs) (continued) TORTION HARMONIC DISTORTION HAR

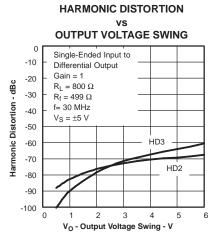


Figure 10.

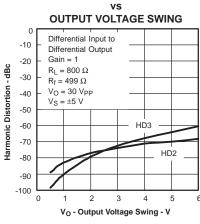


Figure 11.

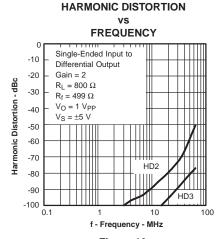


Figure 12.

#### HARMONIC DISTORTION vs FREQUENCY

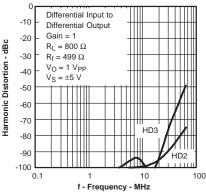


Figure 13.

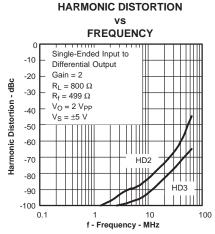


Figure 14.

# HARMONIC DISTORTION vs

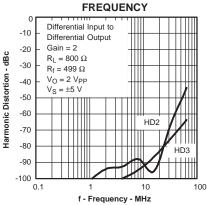


Figure 15.

### HARMONIC DISTORTION

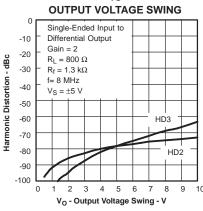


Figure 16.

### HARMONIC DISTORTION vs

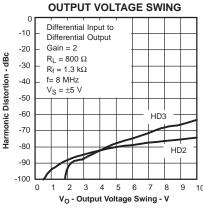


Figure 17.

#### HARMONIC DISTORTION

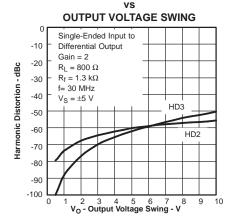
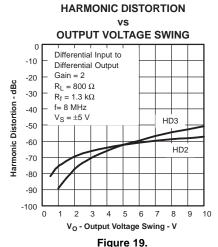
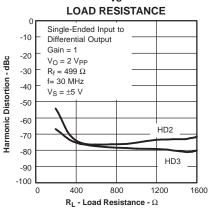


Figure 18.





HARMONIC DISTORTION



HARMONIC DISTORTION

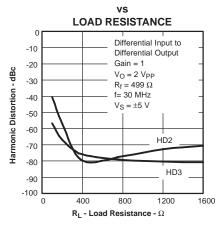
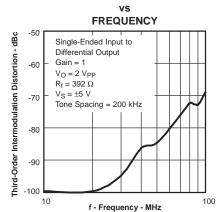


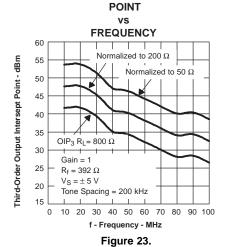
Figure 20.

Figure 21.

#### THIRD-ORDER INTERMODULATION DISTORTION



THIRD-ORDER OUTPUT INTERCEPT



**SLEW RATE** 

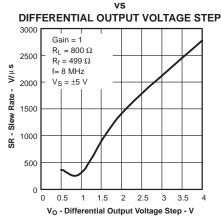
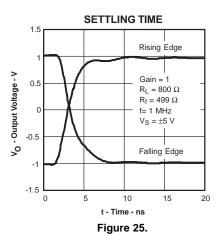


Figure 22.



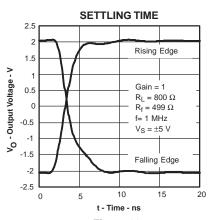


Figure 24.

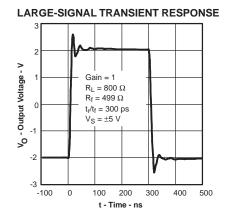
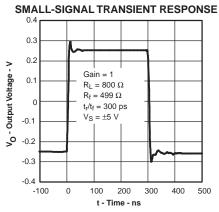
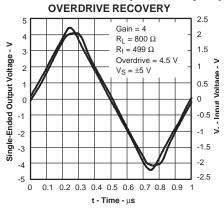


Figure 26.

Figure 27.







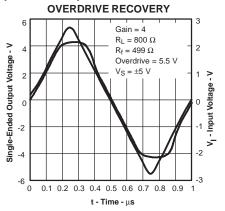
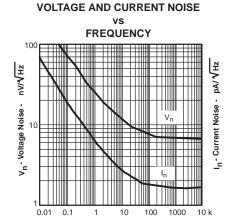


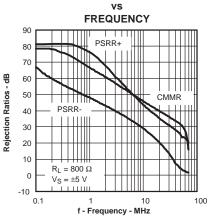
Figure 28.

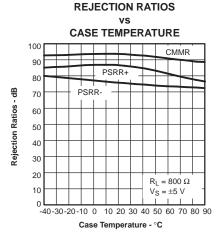
Figure 29.

**REJECTION RATIOS** 

Figure 30.



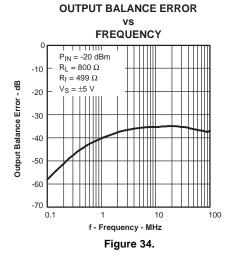


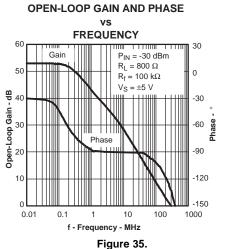


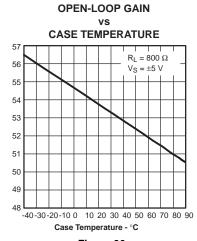
f - Frequency - kHz Figure 31.

Figure 32.

Figure 33.



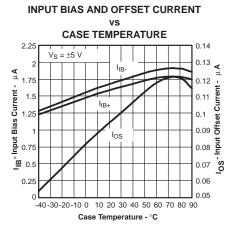




Open-Loop Gain -

Figure 36.





QUIESCENT CURRENT **SUPPLY VOLTAGE** 35 T<sub>A</sub> = 85°C 30  $T_A = 25^{\circ}C$ μ 25 Quiescent Current T<sub>A</sub> = -40°C 20 0 0.5 1.5 2 2.5 3 3.5 4 4.5 5  $V_{\mbox{\scriptsize S}}$  - Supply Voltage -  $\pm V$ 

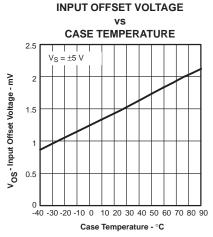
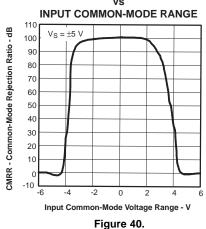


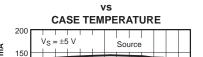
Figure 37.

Figure 38.

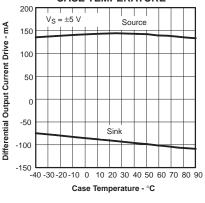
Figure 39.

**COMMON-MODE REJECTION RATIO** 





**DIFFERENTIAL OUTPUT CURRENT DRIVE** 



HARMONIC DISTORTION **OUTPUT COMMON-MODE VOLTAGE** 

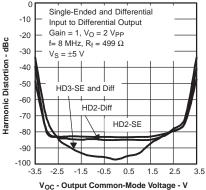
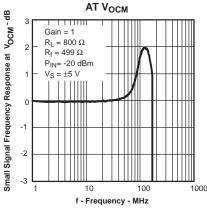
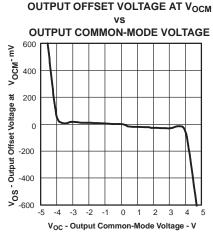


Figure 41.

Figure 42.

#### **SMALL SIGNAL FREQUENCY RESPONSE**





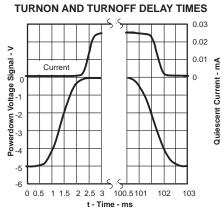
**QUIESCENT CURRENT POWER-DOWN VOLTAGE** 30 25 20 15 10 -4 -3.5 -3 -2.5 -2 -1.5 -1 -0.5 0 Power-Down Voltage - V

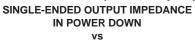
Figure 43.

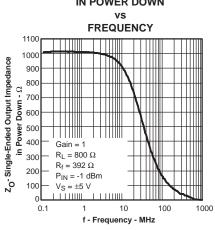
Figure 44.

Figure 45.









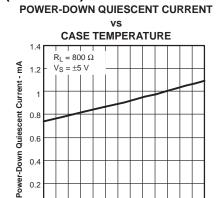


Figure 46.

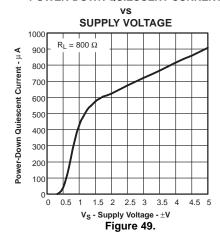
Figure 47.

Figure 48.

-40 -30 -20 -10 0 10 20 30 40 50 60 70 80 90

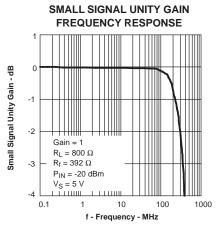
Case Temperature - °C

#### POWER-DOWN QUIESCENT CURRENT

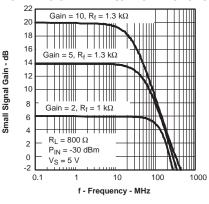




#### TYPICAL CHARACTERISTICS (5 V GRAPHS)



SMALL SIGNAL FREQUENCY RESPONSE



0.1 dB GAIN FLATNESS FREQUENCY RESPONSE

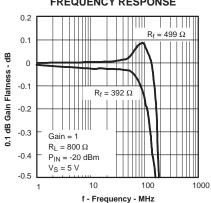
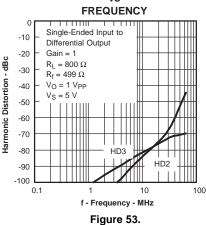


Figure 51.

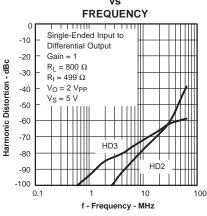
Figure 52.



Figure 50.



HARMONIC DISTORTION



HARMONIC DISTORTION

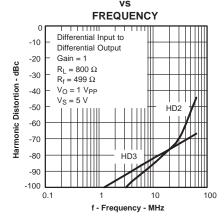
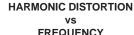
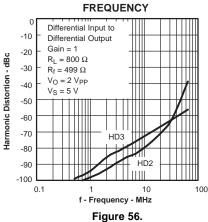


Figure 54.

Figure 55.





# HARMONIC DISTORTION vs OUTPUT VOLTAGE SWING

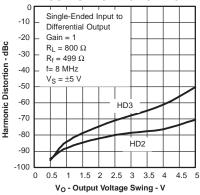


Figure 57.

# HARMONIC DISTORTION vs OUTPUT VOLTAGE SWING

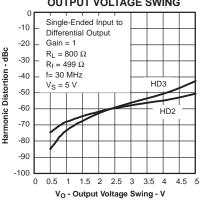
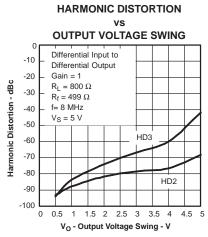


Figure 58.

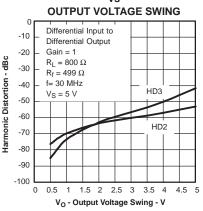
HARMONIC DISTORTION



#### TYPICAL CHARACTERISTICS (5 V GRAPHS) (continued)



HARMONIC DISTORTION **OUTPUT VOLTAGE SWING** 



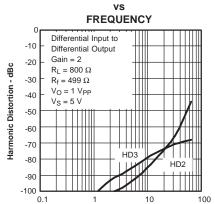
**FREQUENCY** Single-Ended Input to -10 Differential Output -20 Gain = 2 dВс  $R_L = 800 \Omega$ -30  $R_f = 499 \Omega$ Harmonic Distortion V<sub>O</sub> = 1 V<sub>PP</sub> -40 -50 -60 -70 -80 HD3 -90 -100 0.1 100

Figure 59.

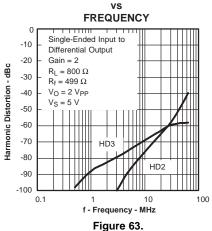
Figure 60.

f - Frequency - MHz Figure 61.

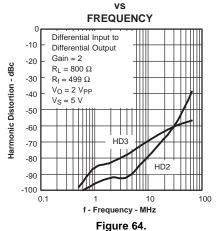
#### HARMONIC DISTORTION



HARMONIC DISTORTION

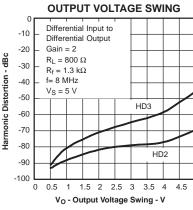


HARMONIC DISTORTION

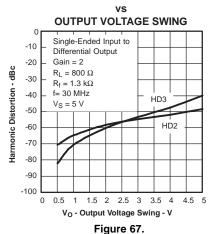


f - Frequency - MHz Figure 62.

### HARMONIC DISTORTION



HARMONIC DISTORTION



HARMONIC DISTORTION

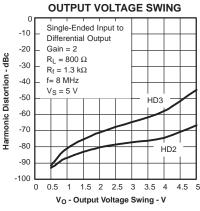
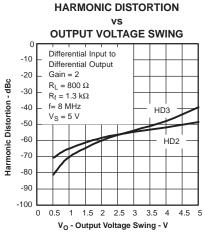


Figure 65.

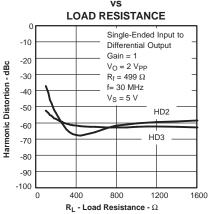
Figure 66.



#### TYPICAL CHARACTERISTICS (5 V GRAPHS) (continued)



HARMONIC DISTORTION



HARMONIC DISTORTION

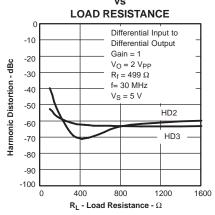
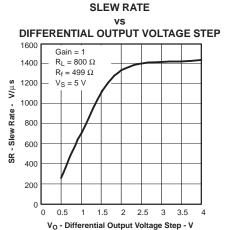


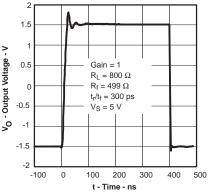
Figure 68.

Figure 69.

Figure 70.



LARGE-SIGNAL TRANSIENT RESPONSE



**SMALL-SIGNAL TRANSIENT RESPONSE** 

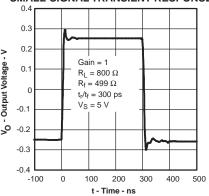


Figure 71.

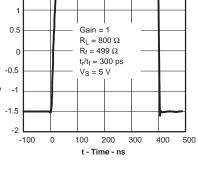
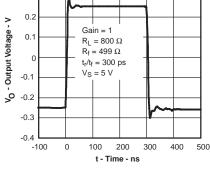


Figure 72.



**VOLTAGE AND CURRENT NOISE** 

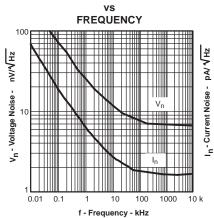


Figure 74.

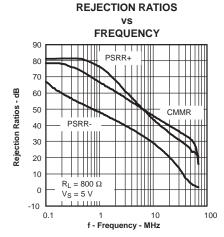


Figure 75.



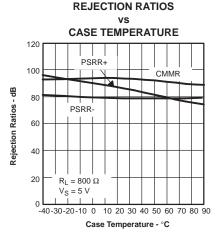
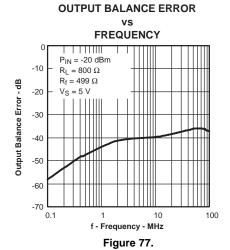


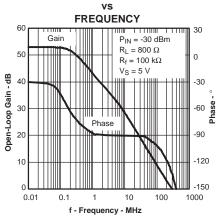
Figure 76.



### TYPICAL CHARACTERISTICS (5 V GRAPHS) (continued)



**OPEN-LOOP GAIN AND PHASE** 



Open-Loop Gain - dB



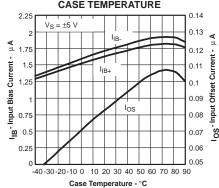
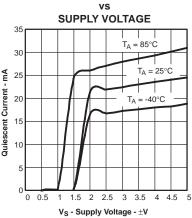


Figure 78.

QUIESCENT CURRENT



**INPUT OFFSET VOLTAGE** 

Figure 79.

-40-30-20-10 0 10 20 30 40 50 60 70 80 90

Case Temperature - °C

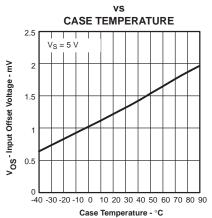


Figure 80.

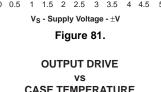
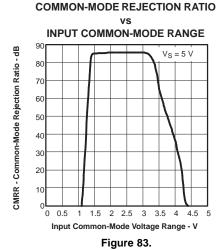


Figure 82.

HARMONIC DISTORTION



CASE TEMPERATURE

150
VS = 5 V
Source

100
Sink
-100
-150
-40-30-20-10 0 10 20 30 40 50 60 70 80 90

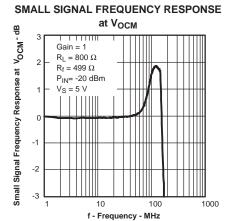
**OUTPUT COMMON-MODE VOLTAGE** Single-Ended and -10 Differential Input -20 Gain = 1  $V_O = 2 V_{PP}$ Harmonic Distortion - dBc -30  $R_f = 499 \Omega$ f= 8 MHz -40  $V_S = 5 V$ -50 HD3-Diff HD2-SE -60 HD2-Diff -70 -80 -90 -100 2 2.25 2.5 2.75 3 V<sub>OCM</sub> - Output Common-Mode Voltage - V

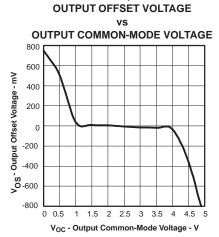
Case Temperature - °C Figure 84.

Figure 85.

# **NSTRUMENTS**

#### TYPICAL CHARACTERISTICS (5 V GRAPHS) (continued)





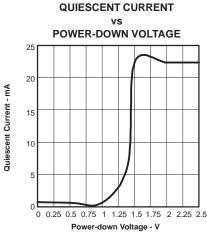
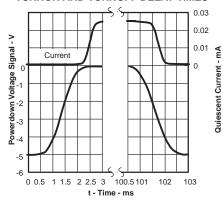


Figure 86.

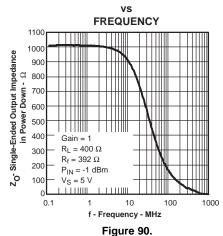
Figure 87.

Figure 88.

#### **TURNON AND TURNOFF DELAY TIMES**







**POWER-DOWN QUIESCENT CURRENT** 

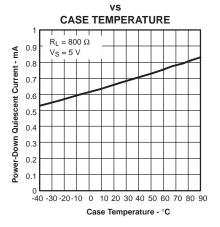


Figure 89.

**POWER-DOWN QUIESCENT CURRENT** 

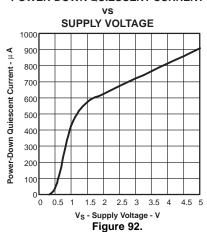


Figure 91.



#### APPLICATION INFORMATION

## MAXIMUM DIE TEMPERATURE TO PREVENT OSCILLATION

The THS4502 and THS4503 may have low level oscillation when the die temperature (also called junction temperature) exceeds +60°C and is not recommended for new designs where the die temperature is expected to exceed +60°C.

The oscillation is due to internal design and external configuration is not expected to mitigate or reduce the problem. This problem is random due to normal process variations and normal testing cannot identify problem units.

The THS4500 and THS4501 are recommended replacement devices.

The die temperature depends on the power dissipation and the thermal resistance of the device and can be approximated with the following formula:

Die Temperature =  $P_{DISS} \times \theta J_A + T_A$ Where:

$$P_{DISS} \approx (V_{S \text{ (TOTAL)}} \times I_{Q}) + (V_{S+} - V_{OUT}) \times I_{OUT}$$

Table 1 shows the estimated maximum ambient temperature ( $T_A$  max) in °C for each package option of the THS4502 and THS4503 using the thermal dissipation rating given in the PACKAGE DISSIPATION RATINGS table for a JEDEC standard High-K test PCB. For each case shown,  $V_{S_{\text{CIOTAL}}}$  =

#### **FULLY DIFFERENTIAL AMPLIFIERS**

Differential signaling offers a number of performance advantages in high-speed analog signal processing systems, including immunity to external common-mode noise, suppression of even-order nonlinearities, and increased dynamic range. Fully differential amplifiers not only serve as the primary means of providing gain to a differential signal chain, but also provide a monolithic solution for converting single-ended signals into differential signals for easier, higher performance processing. The THS4500 family of amplifiers contains products in Texas Instruments' expanding line of high-performance fully differential amplifiers. Information on fully differential amplifier fundamentals, as well as implementation specific information, is presented in the applications section of this data sheet to provide a better understanding of the operation of the THS4500 family of devices, and to simplify the design process for designs using these amplifiers.

#### **Applications Section**

- Fully Differential Amplifier Terminal Functions
- Input Common-Mode Voltage Range and the THS4500 Family

10V,  $R_L = 800~\Omega$  differential, and the quiescent current = 32mA (the maximum over 0°C to 70°C temperature range). The last entry for each package option lists the worst case where the output voltage is 5V DC.

Table 1. Estimated Maximum Ambient Temperature Per Package Option

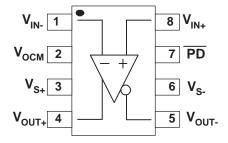
PACKAGE/DEVICE	V <sub>out</sub>	ΘJ <sub>A</sub>	T <sub>A</sub> MAX
SOIC	0V		28.8°C
	2 Vpp		28.0°C
THS4502D	4 Vpp	97.5°C/W	27.3°C
THS4503D	6 Vpp	97.5 C/VV	26.8°C
	8 Vpp		26.3°C
Worst Case =>	5 DC		25.8°C
PWR Pad MSOP	0V	58.4°C/W	41.3°C
	2 Vpp		40.8°C
THS4502DGN	4 Vpp		40.4°C
THS4503DGN	6 Vpp		40.1°C
	8 Vpp		39.8°C
Worst Case =>	5 DC		39.5°C
MSOP	0V		-23.2°C
	2 Vpp	-25.3°C	
THS4502DGK	4 Vpp	260°C/W	-27.1°C
THS4503DGK	6 Vpp	260 C/VV	-28.6°C
	8 Vpp		-29.8°C
Worst Case =>	5 DC		-31.3°C

- Choosing the Proper Value for the Feedback and Gain Resistors
- Application Circuits Using Fully Differential Amplifiers
- Key Design Considerations for Interfacing to an Analog-to-Digital Converter
- Setting the Output Common-Mode Voltage With the V<sub>OCM</sub> Input
- Saving Power With Power-Down Functionality
- Linearity: Definitions, Terminology, Circuit Techniques, and Design Tradeoffs
- An Abbreviated Analysis of Noise in Fully Differential Amplifiers
- Printed-Circuit Board Layout Techniques for Optimal Performance
- Power Dissipation and Thermal Considerations
- Power Supply Decoupling Techniques and Recommendations
- Evaluation Fixtures, Spice Models, and Applications Support
- Additional Reference Material



### FULLY DIFFERENTIAL AMPLIFIER TERMINAL FUNCTIONS

Fully differential amplifiers are typically packaged in eight-pin packages as shown in the diagram. The device pins include two inputs  $(V_{IN+}, V_{IN-})$ , two outputs  $(V_{OUT-}, V_{OUT+})$ , two power supplies  $(V_{S+}, V_{S-})$ , an output common-mode control pin  $(V_{OCM})$ , and an optional power-down pin (PD).

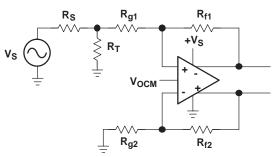


Fully Differential Amplifier Pin Diagram

A standard configuration for the device is shown in the figure. The functionality of a fully differential amplifier can be imagined as two inverting amplifiers that share a common noninverting terminal (though the voltage is not necessarily fixed). For more information on the basic theory of operation for fully differential amplifiers, refer to the Texas Instruments application note titled *Fully Differential Amplifiers*, literature number SLOA054.

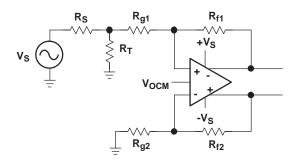
### INPUT COMMON-MODE VOLTAGE RANGE AND THE THS4500 FAMILY

The key difference between the THS4500/1 and the THS4502/3 is the input common-mode range for the two devices. The THS4502 and THS4503 have an input common-mode range that is centered around midrail, and the THS4500 and THS4501 have an input common-mode range that is shifted to include the negative power supply rail. Selection of one or the other is determined by the nature of the application. Specifically, the THS4500 and THS4501 are designed for use in single-supply applications where the input signal is ground-referenced, as depicted in Figure 93. The THS4502 and THS4503 are designed for use in single-supply or split-supply applications where the input signal is centered between the power supply voltages, as depicted in Figure 94.



Application Circuit for the THS4500 and THS4501, Featuring Single-Supply Operation With a Ground-Referenced Input Signal

#### Figure 93.



Application Circuit for the THS4500 and THS4501, Featuring Split-Supply Operation With an Input Signal Referenced at the Midrail

Figure 94.

Equations 1-5 allow for calculation of the required input common-mode range for a given set of input conditions.

The equations allow calculation of the input common-mode range requirements given information about the input signal, the output voltage swing, the gain, and the output common-mode voltage. Calculating the maximum and minimum voltage required for  $V_N$  and  $V_P$  (the amplifier's input nodes) determines whether or not the input common-mode range is violated or not. Four equations are required. Two calculate the output voltages and two calculate the node voltages at  $V_N$  and  $V_P$  (note that only one of these needs calculation, as the amplifier forces a virtual short between the two nodes).

$$V_{OUT+} = \frac{V_{IN+}(1-\beta)-V_{IN-}(1-\beta) + 2V_{OCM}\beta}{2\beta}$$
 (1)

$$V_{\text{OUT-}} = \frac{-V_{\text{IN}+}(1-\beta) + V_{\text{IN-}}(1-\beta) + 2V_{\text{OCM}}\beta}{2\beta}$$
 (2)



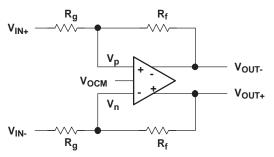
$$V_{N} = V_{IN-}(1-\beta) + V_{OUT+}\beta$$
(3)

Where: 
$$\beta = \frac{R_G}{R_F + R_G}$$
 (4)

$$V_{P} = V_{IN+}(1-\beta) + V_{OUT-}\beta$$
 (5)

#### **NOTE**

The equations denote the device inputs as  $V_N$  and  $V_P$ , and the *circuit* inputs as  $V_{IN+}$  and  $V_{IN-}$ .



**Diagram For Input Common-Mode Range Equations** 

Figure 95.

The two tables below depict the input common-mode range requirements for two different input scenarios, an input referenced around the negative rail and an input referenced around midrail. The tables highlight the differing requirements on input common-mode range, and illustrate reasoning for choosing either the THS4500/1 or the THS4502/3. For signals referenced around the negative power supply, the THS4500/1 should be chosen since its input common-mode range includes the negative supply rail. For all other situations, the THS4502/3 offers slightly improved distortion and noise performance for applications with input signals centered between the power supply rails.

Table 2. Negative-Rail Referenced

Gain (V/V)	V <sub>IN+</sub> (V)	v <sup>k</sup> (>	V <sub>IN</sub> (V <sub>PP</sub> )	V <sub>осм</sub> (V)	V <sub>OD</sub> (V <sub>PP</sub> )	V <sub>NMIN</sub> (V)	V <sub>NMAX</sub> (V)
1	-2.0 to 2.0	0	4	2.5	4	0.75	1.75
2	-1.0 to 1.0	0	2	2.5	4	0.5	1.167
4	-0.5 to 0.5	0	1	2.5	4	0.3	0.7
8	-0.25 to 0.25	0	0.5	2.5	4	0.167	0.389

#### Table 2. Negative-Rail Referenced (continued)

(*/*)   (*)   (*)   (*PP)   (*)   (*PP)   (*)		Gain (V/V)	V <sub>IN+</sub> (V)	V <sub>IN-</sub> (V)	V <sub>IN</sub> (V <sub>PP</sub> )	V <sub>OCM</sub> (V)	V <sub>OD</sub> (V <sub>PP</sub> )		V <sub>NMAX</sub> (V)
---	--	---------------	-------------------------	-------------------------	---------------------------------------	-------------------------	---------------------------------------	--	--------------------------

NOTE: This table assumes a negative-rail referenced, single-ended input signal on a single 5-V supply as shown in Figure 93.  $V_{NMIN} = V_{PMIN}$  and  $V_{NMAX} = V_{PMAX}$ 

**Table 3. Midrail Referenced** 

Gain (V/V)	V <sub>IN+</sub> (V)	V <sub>IN-</sub> (V)	V <sub>IN</sub> (V <sub>PP</sub> )	V <sub>OCM</sub> (V)	V <sub>OD</sub> (V <sub>PP</sub> )	V <sub>NMIN</sub> (V)	V <sub>NMAX</sub> (V)
1	0.5 to 4.5	2.5	4	2.5	4	2	3
2	1.5 to 3.5	2.5	2	2.5	4	2.16	2.83
4	2.0 to 3.0	2.5	1	2.5	4	2.3	2.7
8	2.25 to 2.75	2.5	0.5	2.5	4	2.389	2.61

NOTE: This table assumes a midrail referenced, single-ended input signal on a single 5-V supply.  $V_{NMIN} = V_{PMIN}$  and  $V_{NMAX} = V_{PMAX}$ 

### CHOOSING THE PROPER VALUE FOR THE FEEDBACK AND GAIN RESISTORS

The selection of feedback and gain resistors impacts circuit performance in a number of ways. The values in this section provide the optimum high frequency performance (lowest distortion, flat frequency response). Since the THS4500 family of amplifiers is developed with a voltage feedback architecture, the choice of resistor values does not have a dominant effect on bandwidth, unlike a current feedback amplifier. However, resistor choices do have second-order effects. For optimal performance, the following feedback resistor values are recommended. In higher gain configurations (gain greater than two), the feedback resistor values have much less effect on the high frequency performance. Example feedback and gain resistor values are given in the section on basic design considerations (Table 4).

Amplifier loading, noise, and the flatness of the frequency response are three design parameters that should be considered when selecting feedback resistors. Larger resistor values contribute more noise and can induce peaking in the ac response in low gain configurations, and smaller resistor values can load the amplifier more heavily, resulting in a reduction in distortion performance. In addition, feedback resistor values, coupled with gain requirements, determine the value of the gain resistors, directly impacting the input impedance of the entire circuit. While there are no strict rules about resistor selection, these trends can provide qualitative design guidance.

### APPLICATION CIRCUITS USING FULLY DIFFERENTIAL AMPLIFIERS

Fully differential amplifiers provide designers with a great deal of flexibility in a wide variety of applications. This section provides an overview of some common circuit configurations and gives some design guidelines. Designing the interface to an ADC, driving lines differentially, and filtering with fully differential amplifiers are a few of the circuits that are covered.

#### **BASIC DESIGN CONSIDERATIONS**

The circuits in Figures 96 through 100 are used to highlight basic design considerations for fully differential amplifier circuit designs.

Table 4. Resistor Values for Balanced Operation in Various Gain Configurations

Gain $\left(\frac{V_{OD}}{V_{IN}}\right)$ R2 & R4 ( $\Omega$ ) R1 ( $\Omega$ ) R3 ( $\Omega$ ) R <sub>T</sub> ( $\Omega$ )										
1	392	412	383	54.9						
1	499	523	487	53.6						
2	392	215	187	60.4						
2	1.3k	665	634	52.3						
5 1.3k 274 249 56.2										
5	3.32k	681	649	52.3						
10	1.3k	147	118	64.9						
10	6.81k	698	681	52.3						
NOTE: Values i	NOTE: Values in this table assume a 50 Ω source impedance.									

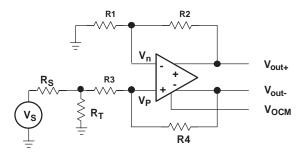


Figure 96.

Equations for calculating fully differential amplifier resistor values in order to obtain balanced operation in the presence of a  $50-\Omega$  source impedance are given in equations 6 through 9.

$$R_{T} = \frac{1}{\frac{1}{R_{S}} - \frac{1 - \frac{K}{2(1 + K)}}{R3}} \qquad K = \frac{R2}{R1} \quad R2 = R4$$

$$R3 = R1 - (R_{s} || R_{T})$$
(6)

$$\beta_{1} = \frac{R1}{R1 + R2} \ \beta_{2} = \frac{R3 + R_{T} \parallel R_{S}}{R3 + R_{T} \parallel R_{S} + R4}$$
 (7)

$$\frac{V_{OD}}{V_S} = 2\left(\frac{1-\beta_2}{\beta_1 + \beta_2}\right) \left(\frac{R_T}{R_T + R_S}\right)$$
(8)

$$\frac{V_{OD}}{V_{IN}} = 2\left(\frac{1-\beta_2}{\beta_1 + \beta_2}\right) \tag{9}$$

For more detailed information about balance in fully differential amplifiers, see *Fully Differential Amplifiers*, referenced at the end of this data sheet.

## INTERFACING TO AN ANALOG-TO-DIGITAL CONVERTER

The THS4500 family of amplifiers are designed specifically to interface to today's highest-performance analog-to-digital converters. This section highlights the key concerns when interfacing to an ADC and provides example ADC/fully differential amplifier interface circuits.

Key design concerns when interfacing to an analog-to-digital converter:

- Terminate the input source properly. In high-frequency receiver chains, the source feeding the fully differential amplifier requires a specific load impedance (e.g.,  $50\Omega$ ).
- Design a symmetric printed-circuit board layout. Even-order distortion products are heavily influenced by layout, and careful attention to a symmetric layout will minimize these distortion products.
- Minimize inductance in power supply decoupling traces and components. Poor power supply decoupling can have a dramatic effect on circuit performance. Since the outputs are differential, differential currents exist in the power supply pins. Thus, decoupling capacitors should be placed in a manner that minimizes the impedance of the current loop.
- Use separate analog and digital power supplies and grounds. Noise (bounce) in the power supplies (created by digital switching currents) can couple directly into the signal path, and power supply noise can create higher distortion products as well.
- Use care when filtering. While an RC low-pass filter may be desirable on the output of the amplifier to filter broadband noise, the excess loading can negatively impact the amplifier linearity. Filtering in the feedback path does not have this effect.
- AC-coupling allows easier circuit design. If dc-coupling is required, be aware of the excess power dissipation that can occur due to level-shifting the output through the output

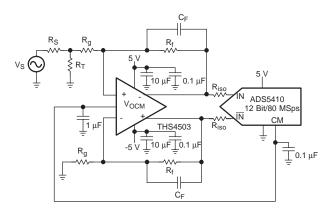


common-mode voltage control.

- Do not terminate the output unless required. Many open-loop, class-A amplifiers require 50-Ω termination for proper operation, but closed-loop fully differential amplifiers drive a specific output voltage regardless of the load impedance present. Terminating the output of a fully differential amplifier with a heavy load adversely effects the amplifier's linearity.
- Comprehend the V<sub>OCM</sub> input drive requirements. Determine if the ADC's voltage reference can provide the required amount of current to move V<sub>OCM</sub> to the desired value. A buffer may be needed.
- Decouple the V<sub>OCM</sub> pin to eliminate the antenna effect. V<sub>OCM</sub> is a high-impedance node that can act as an antenna. A large decoupling capacitor on this node eliminates this problem.
- Be cognizant of the input common-mode range. If the input signal is referenced around the negative power supply rail (e.g., around ground on a single 5 V supply), then the THS4500/1 accommodates the input signal. If the input signal is referenced around midrail, choose the THS4502/3 for the best operation.
- Packaging makes a difference at higher frequencies. If possible, choose the smaller, thermally enhanced MSOP package for the best performance. As a rule, lower junction temperatures provide better performance. If possible, use a thermally enhanced package, even if the power dissipation is relatively small compared to the maximum power dissipation rating to achieve the best results.
- Comprehend the effect of the load impedance seen by the fully differential amplifier when performing system-level intercept point calculations. Lighter loads (such as those presented by an ADC) allow smaller intercept points to support the same level of intermodulation distortion performance.

# **EXAMPLE ANALOG-TO-DIGITAL CONVERTER DRIVER CIRCUITS**

The THS4500 family of devices is designed to drive high-performance ADCs with extremely high linearity, allowing for the maximum effective number of bits at the output of the data converter. Two representative circuits shown below highlight single-supply operation and split supply operation. Specific feedback resistor, gain resistor, and feedback capacitor values are not specified, as their values depend on the frequency of interest. Information on calculating these values can be found in the applications material above.



Using the THS4503 With the ADS5410

Figure 97.

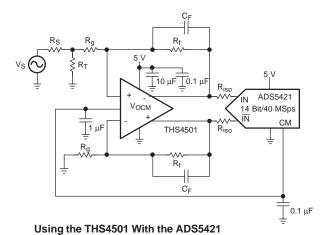
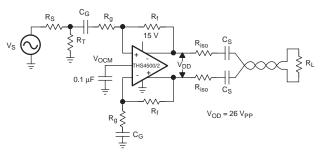


Figure 98.

#### **FULLY DIFFERENTIAL LINE DRIVERS**

The THS4500 family of amplifiers can be used as high-frequency, high-swing differential line drivers. Their high power supply voltage rating (16.5 V absolute maximum) allows operation on a single 12-V or a single 15-V supply. The high supply voltage, coupled with the ability to provide differential outputs enables the ability to drive 26  $V_{PP}$  into reasonably heavy loads (250  $\Omega$  or greater). The circuit in Figure 99 illustrates the THS4500 family of devices used as high speed line drivers. For line driver applications, close attention must be paid to thermal design constraints due to the typically high level of power dissipation.

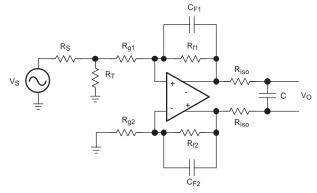


Fully Differential Line Driver With High Output Swing

Figure 99.

#### Filtering With Fully Differential Amplifiers

Similar to their single-ended counterparts, fully differential amplifiers have the ability to couple filtering functionality with voltage gain. Numerous filter topologies can be based on fully differential amplifiers. Several of these are outlined in *A Differential Circuit Collection*, (literature number SLOA064) referenced at the end of this data sheet. The circuit below depicts a simple two-pole low-pass filter applicable to many different types of systems. The first pole is set by the resistors and capacitors in the feedback paths, and the second pole is set by the isolation resistors and the capacitor across the outputs of the isolation resistors.



A Two-Pole, Low-Pass Filter Design Using a Fully Differential Amplifier With Poles Located at:  $P1 = (2\pi R_f C_F)^{-1} \text{ in Hz and P2} = (4\pi R_{iso}C)^{-1} \text{ in Hz}$ 

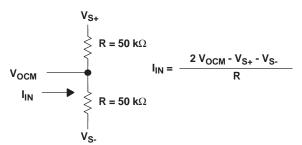
#### Figure 100.

Often times, filters like these are used to eliminate broadband noise and out-of-band distortion products in signal acquisition systems. It should be noted that the increased load placed on the output of the amplifier by the second low-pass filter has a detrimental effect on the distortion performance. The preferred method of filtering is using the feedback network, as the typically smaller capacitances required at these points in the circuit do not load the amplifier nearly as heavily in the pass-band.

# SETTING THE OUTPUT COMMON-MODE VOLTAGE WITH THE $V_{\text{OCM}}$ INPUT

The output common-mode voltage pin provides a critical function to the fully differential amplifier; it accepts an input voltage and reproduces that input voltage as the output common-mode voltage. In other words, the  $V_{\rm OCM}$  input provides the ability to level-shift the outputs to any voltage inside the output voltage swing of the amplifier.

A description of the input circuitry of the V<sub>OCM</sub> pin is shown below to facilitate an easier understanding of the V<sub>OCM</sub> interface requirements. The V<sub>OCM</sub> pin has two 50-k $\Omega$  resistors between the power supply rails to set the default output common-mode voltage to midrail. A voltage applied to the V<sub>OCM</sub> pin alters the output common-mode voltage as long as the source has the ability to provide enough current to overdrive the two 50-k $\Omega$  resistors. This phenomenon is depicted in the V<sub>OCM</sub> equivalent circuit diagram. The table contains some representative examples to aid in determining the current drive requirement for the V<sub>OCM</sub> voltage source. This parameter is especially important when using the reference voltage of an analog-to-digital converter to drive V<sub>OCM</sub>. Output current drive capabilities differ from part to part, so a voltage buffer may be necessary in some applications.



Equivalent Input Circuit for Voca

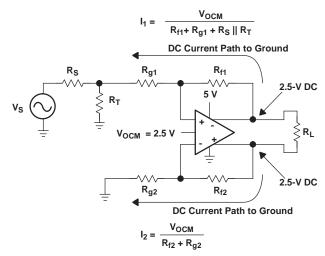
Figure 101.

By design, the input signal applied to the V<sub>OCM</sub> pin propagates to the outputs as a common-mode signal. As shown in the equivalent circuit diagram, the V<sub>OCM</sub> input has a high impedance associated with it, dictated by the two 50-k $\Omega$  resistors. While the high impedance allows for relaxed drive requirements, it also allows the pin and any associated printed-circuit board traces to act as an antenna. For this reason, a decoupling capacitor is recommended on this node for the sole purpose of filtering any high frequency noise that could couple into the signal path through the V<sub>OCM</sub> circuitry. A 0.1-µF or 1-µF capacitance is a reasonable value for eliminating a great deal of but additional, broadband interference, decoupling capacitors should be considered if a



specific source of electromagnetic or radio frequency interference is present elsewhere in the system. Information on the ac performance (bandwidth, slew rate) of the  $V_{\rm OCM}$  circuitry is included in the specification table and graph section.

Since the V<sub>OCM</sub> pin provides the ability to set an output common-mode voltage, the ability for increased power dissipation exists. While this does not pose a performance problem for the amplifier, it can cause additional power dissipation of which the system designer should be aware. The circuit shown in Figure 102 demonstrates an example of this phenomenon. For a device operating on a single 5-V supply with an input signal referenced around ground and an output common-mode voltage of 2.5 V, a dc potential exists between the outputs and the inputs of the device. The amplifier sources current into the feedback network in order to provide the circuit with the proper operating point. While there are no serious effects on the circuit performance, the extra power dissipation may need to be included in the system's power budget.



Depiction of DC Power Dissipation Caused By Output Level-Shifting in a DC-Coupled Circuit

Figure 102.

# SAVING POWER WITH POWER-DOWN FUNCTIONALITY

The THS4500 family of fully differential amplifiers contains devices that come with and without the power-down option. Even-numbered devices have power-down capability, which is described in detail here.

The power-down pin of the amplifiers defaults to the positive supply voltage in the absence of an applied voltage (i.e. an internal pullup resistor is present), putting the amplifier in the *power-on* mode of

operation. To turn off the amplifier in an effort to conserve power, the power-down pin can be driven towards the negative rail. The threshold voltages for power-on and power-down are relative to the supply rails and given in the specification tables. Above the enable threshold voltage, the device is on. Below the disable threshold voltage, the device is off. Behavior in between these threshold voltages is not specified.

Note that this power-down functionality is just that; the amplifier consumes less power in power-down mode. The power-down mode is not intended to provide a high-impedance output. In other words, the power-down functionality is not intended to allow use as a 3-state bus driver. When in power-down mode, the impedance looking back into the output of the amplifier is dominated by the feedback and gain setting resistors.

The time delays associated with turning the device on and off are specified as the time it takes for the amplifier to reach 50% of the nominal quiescent current. The time delays are on the order of microseconds because the amplifier moves in and out of the linear mode of operation in these transitions.

# LINEARITY; DEFINITIIONS, TERMINOLOGY, CIRCUIT TECHNIQUES, AND DESIGN TRADEOFFS

The THS4500 family of devices features unprecedented distortion performance for monolithic fully differential amplifiers. This section focuses on the fundamentals of distortion, circuit techniques for reducing nonlinearity, and methods for equating distortion of fully differential amplifiers to desired linearity specifications in RF receiver chains.

Amplifiers are generally thought of as linear devices. In other words, the output of an amplifier is a linearly scaled version of the input signal applied to it. In reality, however, amplifier transfer functions are nonlinear. Minimizing amplifier nonlinearity is a primary design goal in many applications.

Intercept points are specifications that have long been used as key design criteria in the RF world as a metric communications intermodulation distortion performance of a device in the signal chain (e.g., amplifiers, mixers, etc.). Use of the intercept point, rather than strictly intermodulation distortion, allows for simpler system-level calculations. Intercept points, like noise figures, can be easily cascaded back and forth through a signal chain to determine the overall receiver chain's intermodulation distortion performance. relationship between The intermodulation distortion and intercept point is depicted in Figure 103 and Figure 104.

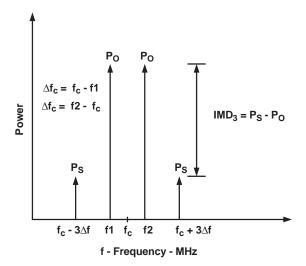


Figure 103.

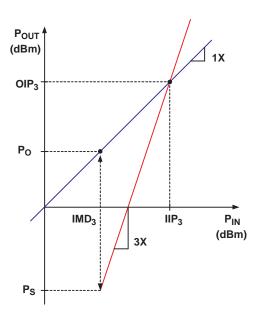


Figure 104.

Due to the intercept point's ease of use in system level calculations for receiver chains, it has become the specification of choice for guiding distortion-related design decisions. Traditionally, these systems use primarily class-A, single-ended RF amplifiers as gain blocks. These RF amplifiers are typically designed to operate in a 50- $\Omega$  environment, just like the rest of the receiver chain. Since intercept points are given in dBm, this implies an associated impedance (50  $\Omega$ ).

However, with a fully differential amplifier, the output does not require termination as an RF amplifier would. Because closed-loop amplifiers deliver signals to their outputs regardless of the impedance present, it is important to comprehend this when evaluating the intercept point of a fully differential amplifier. The THS4500 series of devices yields optimum distortion performance when loaded with 200  $\Omega$  to 1  $k\Omega$ , very similar to the input impedance of an analog-to-digital converter over its input frequency band. As a result, terminating the input of the ADC to 50  $\Omega$  can actually be detrimental to system performance.

This discontinuity between open-loop, class-A amplifiers and closed-loop, class-AB amplifiers becomes apparent when comparing the intercept points of the two types of devices. Equation 10 gives the definition of an intercept point, relative to the intermodulation distortion.

$$OIP_3 = P_O + \left(\frac{|IMD_3|}{2}\right)$$
 where (10)

$$P_{O} = 10 \log \left( \frac{V_{Pdiff}^{2}}{2R_{L} \times 0.001} \right)$$
 (11)

#### **NOTE**

 $P_o$  is the output power of a single tone,  $R_L$  is the differential load resistance, and  $V_{P(diff)}$  is the differential peak voltage for a single tone.

As can be seen in the equation, when a higher impedance is used, the same level of intermodulation distortion performance results in a lower intercept point. Therefore, it is important to comprehend the impedance seen by the output of the fully differential amplifier when selecting a minimum intercept point. The graphic below shows the relationship between the strict definition of an intercept point with a normalized, or equivalent, intercept point for the THS4502.



#### THIRD-ORDER OUTPUT INTERCEPT POINT

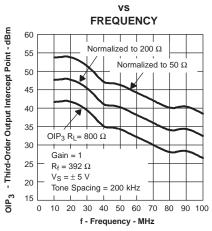


Figure 105.

Comparing specifications between different device types becomes easier when a common impedance level is assumed. For this reason, the intercept points on the THS4500 family of devices are reported normalized to a  $50-\Omega$  load impedance.

### AN ANALYSIS OF NOICE IN FULLY DIFFERENTIAL AMPLIFIERS

Noise analysis in fully differential amplifiers is analogous to noise analysis in single-ended amplifiers. The same concepts apply. Below, a generic circuit diagram consisting of a voltage source, a termination resistor, two gain setting resistors, two feedback resistors, and a fully differential amplifier is shown, including all the relevant noise sources. From this circuit, the noise factor (F) and noise figure (NF) are calculated. The figures indicate the appropriate scaling factor for each of the noise sources in two different cases. The first case includes the termination resistor, and the second, simplified case assumes that the voltage source is properly terminated by the gain-setting resistors. With these scaling factors, the amplifier's input noise power (N<sub>A</sub>) can be calculated by summing each individual noise source with its scaling factor. The noise delivered to the amplifier by the source (N<sub>I</sub>) and input noise power are used to calculate the noise factor and noise figure as shown in equations 23 through 27.

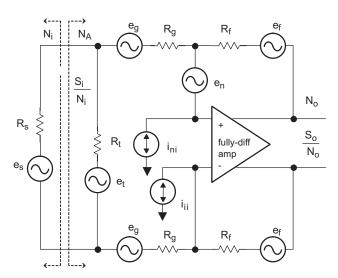


Figure 106. Noise Sources in a Fully Differential Amplifier Circuit

N<sub>A</sub>: Fully Differential Amplifier

Noise

Source Scale Factor

$$(e_{ni})^{2} \qquad \left[\frac{R_{g}}{R_{f}} + \frac{R_{g}}{R_{g} + \frac{R_{s}R_{t}}{2(R_{s} + R_{t})}}\right]^{2}$$
 (12)

$$(i_{ni})^2 \qquad R_g^2 \tag{13}$$

$$(i_{ij})^2 R_g^2 (14)$$

$$4kTR_{t} = \left(\frac{\frac{2R_{s}R_{g}}{R_{s} + 2R_{g}}}{R_{t} + \frac{2R_{s}R_{g}}{R_{s} + 2R_{g}}}\right)^{2}$$
(15)

$$4kTR_{f} 2 \times \left(\frac{R_{g}}{R_{f}}\right)^{2} (16)$$

$$4kTR_{g} 2 \times \left[\frac{R_{g}}{R_{g} + \frac{R_{s}R_{t}}{2(R_{s} + R_{t})}}\right]^{2} (17)$$

Figure 107. Scaling Factors for Individual Noise Sources Assuming a Finite Value Termination Resistor



 $N_A$ : Fully Differential Amplifier; termination =  $2R_g$ Noise

Source Scale Factor

$$(e_{ni})^2$$
  $\left(\frac{R_g}{R_f} + \frac{R_g}{R_g + \frac{R_s}{2}}\right)^2$  (18)

$$(i_{ni})^2 \qquad R_g^2$$
 (19)

$$(i_{ij})^2 \qquad R_g^2 \tag{20}$$

$$4kTR_f 2 \times \left(\frac{R_g}{R_f}\right)^2 (21)$$

$$_{4kTR_g}$$
  $_{2} \times \left[ \frac{R_g}{R_g + \frac{R_s}{2}} \right]^2$  (22)

Figure 108. Scaling Factors for Individual Noise Sources Assuming No termination Resistance is Used (e.g.,  $R_T$  is open)

$$N_{i} = 4kTR_{s} \left[ \frac{2R_{t}R_{g}}{\frac{R_{t} + 2R_{g}}{R_{s} + \frac{2R_{t}R_{g}}{R_{t} + 2R_{g}}}} \right]^{2}$$
(23)

Figure 109. Input Noise With a Termination Resistor

$$N_{i} = 4kTR_{s} \left(\frac{2R_{g}}{R_{s} + 2R_{g}}\right)^{2}$$
 (24)

#### Figure 110. Input Noise Assuming No Termination Resistor

$$N_A = \Sigma(Noise Source \times Scale Factor)$$
 (25)

$$F = 1 + \frac{N_A}{N_L} \tag{26}$$

$$NF = 10 \log (F) \tag{27}$$

Figure 111. Noise Factor and Noise Figure Calculations

# PRINTED-CIRCUIT BOARD LAYOUT TECHNIQUES FOR OPTIMAL PERFORMANCE

Achieving optimum performance with high frequency amplifier-like devices in the THS4500 family requires careful attention to board layout parasitic and external component types.

Recommendations that optimize performance include:

- Minimize parasitic capacitance to any ac ground for all of the signal I/O pins. Parasitic capacitance on the output and input pins can cause instability. To reduce unwanted capacitance, a window around the signal I/O pins should be opened in all of the ground and power planes around those pins. Otherwise, ground and power planes should be unbroken elsewhere on the board.
- Minimize the distance (< 0.25") from the power supply pins to high frequency 0.1-µF decoupling capacitors. At the device pins, the ground and power plane layout should not be in close proximity to the signal I/O pins. Avoid narrow power and ground traces to minimize inductance between the pins and the decoupling capacitors. The power supply connections should always be decoupled with these capacitors. Larger (6.8 µF or more) tantalum decoupling capacitors, effective at lower frequency, should also be used on the main supply pins. These may be placed somewhat farther from the device and may be shared among several devices in the same area of the PC board. The primary goal is to minimize the impedance seen in the differential-current return paths.
- Careful selection and placement of external components preserve the high frequency performance of the THS4500 family. Resistors should be a very low reactance Surface-mount resistors work best and allow a tighter overall layout. Metal-film and carbon composition, axially-leaded resistors can also provide good high frequency performance. Again, keep their leads and PC board trace length as short as possible. Never use wirewound type resistors in a high frequency application. Since the output pin and inverting input pins are the most sensitive to parasitic capacitance, always position the feedback and series output resistors, if any, as close as possible to the inverting input pins and output pins. Other network components, such as input termination resistors, should be placed close to the gain-setting resistors. Even with a low parasitic capacitance shunting the external resistors, excessively high resistor values can create significant time constants that can degrade performance. Good axial metal-film resistors approximately surface-mount have 0.2 pF in shunt with the resistor. For resistor values >  $2.0 \text{ k}\Omega$ , this parasitic capacitance can add a pole and/or a zero below 400 MHz that can



effect circuit operation. Keep resistor values as low as possible, consistent with load driving considerations.

- Connections to other wideband devices on the board may be made with short direct traces or through onboard transmission lines. For short connections, consider the trace and the input to the next device as a lumped capacitive load. Relatively wide traces (50 mils to 100 mils) should be used, preferably with ground and power planes opened up around them. Estimate the total capacitive load and determine if isolation resistors on the outputs are necessary. Low parasitic capacitive loads (< 4 pF) may not need an R<sub>S</sub> since the TH\$4500 family is nominally compensated to operate with a 2-pF parasitic load. Higher parasitic capacitive loads without an Rs are allowed as the signal gain increases (increasing the unloaded phase margin). If a long trace is required, and the 6-dB signal loss intrinsic to a doubly-terminated transmission line is acceptable, implement a matched impedance transmission line using microstrip or stripline techniques (consult an ECL design handbook for microstrip and stripline layout techniques).
- A 50-Ω environment is normally not necessary onboard, and in fact, a higher impedance environment improves distortion as shown in the distortion versus load plots. With a characteristic board trace impedance defined based on board material and trace dimensions, a matching series resistor into the trace from the output of the THS4500 family is used as well as a terminating shunt resistor at the input of the destination device.
- Remember also that the terminating impedance is the parallel combination of the shunt resistor and the input impedance of the destination device: this total effective impedance should be set to match the trace impedance. If the 6-dB attenuation of a doubly terminated transmission line is unacceptable. а long trace can he series-terminated at the source end only. Treat the trace as a capacitive load in this case. This does not preserve signal integrity as well as a doubly-terminated line. If the input impedance of the destination device is low, there is some signal attenuation due to the voltage divider formed by the series output into the terminating impedance.
- Socketing a high speed part like the THS4500 family is not recommended. The additional lead length and pin-to-pin capacitance introduced by the socket can create an extremely troublesome parasitic network which can make it almost impossible to achieve a smooth, stable frequency response. Best results are obtained by soldering the THS4500 family parts directly onto the board.

#### PowerPAD DESIGN CONSIDERATIONS

available The THS4500 family is in thermally-enhanced PowerPAD family of packages. These packages are constructed using a downset leadframe upon which the die is mounted [see Figure 112(a) and Figure 112(b)]. This arrangement results in the lead frame being exposed as a thermal pad on the underside of the package [see Figure 112(c)]. Because this thermal pad has direct thermal contact with the die, excellent thermal performance can be achieved by providing a good thermal path away from the thermal pad.

The PowerPAD package allows for both assembly and thermal management in one manufacturing operation. During the surface-mount solder operation (when the leads are being soldered), the thermal pad can also be soldered to a copper area underneath the package. Through the use of thermal paths within this copper area, heat can be conducted away from the package into either a ground plane or other heat dissipating device.

The PowerPAD package represents a breakthrough in combining the small area and ease of assembly of surface mount with the, heretofore, awkward mechanical methods of heatsinking.

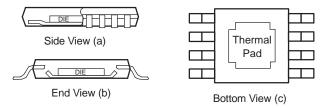


Figure 112. Views of Thermally Enhanced Package

Although there are many ways to properly heatsink the PowerPAD package, the following steps illustrate the recommended approach.

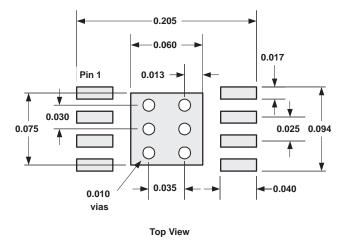


Figure 113. PowerPAD PCB Etch and Via Pattern

# TEXAS INSTRUMENTS

#### PowerPAD PCB LAYOUT CONSIDERATIONS

- 1. Prepare the PCB with a top side etch pattern as shown in Figure 113. There should be etch for the leads as well as etch for the thermal pad.
- Place five holes in the area of the thermal pad.
   These holes should be 13 mils in diameter. Keep them small so that solder wicking through the holes is not a problem during reflow.
- 3. Additional vias may be placed anywhere along the thermal plane outside of the thermal pad area. This helps dissipate the heat generated by the THS4500 family IC. These additional vias may be larger than the 13-mil diameter vias directly under the thermal pad. They can be larger because they are not in the thermal pad area to be soldered so that wicking is not a problem.
- 4. Connect all holes to the internal ground plane.
- 5. When connecting these holes to the ground plane, do not use the typical web or spoke via connection methodology. Web connections have a high thermal resistance connection that is useful for slowing the heat transfer during soldering operations. This makes the soldering of vias that have plane connections easier. In this application, however, low thermal resistance is desired for the most efficient heat transfer. Therefore, the holes under the THS4500 family PowerPAD package should make their connection to the internal ground plane with a complete connection around circumference of the plated-through hole.
- 6. The top-side solder mask should leave the terminals of the package and the thermal pad area with its five holes exposed. The bottom-side solder mask should cover the five holes of the thermal pad area. This prevents solder from being pulled away from the thermal pad area during the reflow process.
- Apply solder paste to the exposed thermal pad area and all of the IC terminals.
- 8. With these preparatory steps in place, the IC is simply placed in position and run through the solder reflow operation as any standard surface-mount component. This results in a part that is properly installed.

# Power Dissipation and Thermal Considerations

The THS4500 family of devices does not incorporate automatic thermal shutoff protection, so the designer must take care to ensure that the design does not violate the absolute maximum junction temperature of the device. Failure may result if the absolute

maximum junction temperature of 150°C is exceeded. For best performance, design for a maximum junction temperature of 125°C. Between 125°C and 150°C, damage does not occur, but the performance of the amplifier begins to degrade.

The thermal characteristics of the device are dictated by the package and the PC board. Maximum power dissipation for a given package can be calculated using the following formula.

$$P_{Dmax} = \frac{T_{max} - T_A}{\theta_{JA}}$$
 (28)

Where:

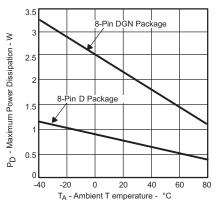
 $P_{Dmax}$  is the maximum power dissipation in the amplifier (W).  $T_{max}$  is the absolute maximum junction temperature (°C).  $T_A$  is the ambient temperature (°C).

 $\theta_{JA} = \theta_{JC} + \theta_{CA}$ 

 $\theta_{JC}$  is the thermal coefficient from the silicon junctions to the case (°C/W).

 $\theta_{CA}$  is the thermal coefficient from the case to ambient air (°C/W).

For systems where heat dissipation is more critical, the THS4500 family of devices is offered in an 8-pin MSOP with PowerPAD. The thermal coefficient for the MSOP PowerPAD package is substantially improved over the traditional SOIC. Maximum power dissipation levels are depicted in the graph for the two packages. The data for the DGN package assumes a board layout that follows the PowerPAD layout guidelines referenced above and detailed in the PowerPAD application notes in the *Additional Reference Material*section at the end of the data sheet.



 $\theta_{JA}$  = 170°C/W for 8-Pin SOIC (D)  $\theta_{JA}$  = 58.4°C/W for 8-Pin MSOP (DGN)

Figure 114. Maximum Power Dissipation vs Ambient Temperature

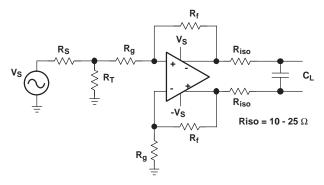
When determining whether or not the device satisfies the maximum power dissipation requirement, it is important to not only consider quiescent power



dissipation, but also dynamic power dissipation. Often times, this is difficult to quantify because the signal pattern is inconsistent, but an estimate of the RMS power dissipation can provide visibility into a possible problem.

#### **DRIVING CAPACITIVE LOADS**

High-speed amplifiers are typically not well-suited for driving large capacitive loads. If necessary, however, the load capacitance should be isolated by two isolation resistors in series with the output. The requisite isolation resistor size depends on the value of the capacitance, but 10 to  $25\Omega$  is a good place to begin the optimization process. Larger isolation resistors decrease the amount of peaking in the frequency response induced by the capacitive load, but this comes at the expense of larger voltage drop across the resistors, increasing the output swing requirements of the system.



Use of Isolation Resistors With a Capacitive Load.

Figure 115.

## POWER SUPPLY DECOUPLING TECHNIQUES AND RECOMMENDATIONS

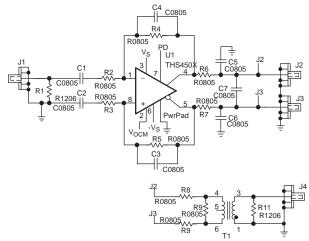
Power supply decoupling is a critical aspect of any high-performance amplifier design process. Careful decoupling provides higher quality ac performance (most notably improved distortion performance). The following guidelines ensure the highest level of performance.

- Place decoupling capacitors as close to the power supply inputs as possible, with the goal of minimizing the inductance of the path from ground to the power supply.
- 2. Placement priority should be as follows: smaller capacitors should be closer to the device.
- 3. Use of solid power and ground planes is recommended to reduce the inductance along power supply return current paths.
- Recommended values for power supply decoupling include 10-μF and 0.1-μF capacitors for each supply. A 1000-pF capacitor can be used across the supplies as well for extremely

high frequency return currents, but often is not required.

### EVALUATION FIXTURES, SPICE MODELS, AND APPLICTIONS SUPPORT

Texas Instruments is committed to providing its customers with the highest quality of applications support. To support this goal, an evaluation board has been developed for the THS4500 family of fully differential amplifiers. The evaluation board can be obtained by ordering through the Texas Instruments web site, www.ti.com, or through your local Texas Instruments sales representative. Schematic for the evaluation board is shown below with their default component values. Unpopulated footprints are shown to provide insight into design flexibility.



Simplified Schematic of the Evaluation Board. Power Supply Decoupling,  $V_{\text{OCM}}$ , and Power Down Circuitry Not Shown

#### Figure 116.

Computer simulation of circuit performance using SPICE is often useful when analyzing performance of analog circuits and systems. This is particularly true for video and RF amplifier circuits where parasitic capacitance and inductance can have a major effect on circuit performance. A SPICE model for the THS4500 family of devices is available through the Texas Instruments web site (www.ti.com). The PIC is also available for design assistance and detailed product information. These models do a good job of predicting small-signal ac and transient performance under a wide variety of operating conditions. They are not intended to model the distortion characteristics of the amplifier, nor do they attempt to distinguish between the package types in small-signal performance. their ac Detailed information about what is and is not modeled is contained in the model file itself.



#### ADDITIONAL REFERENCE MATERIAL

- PowerPAD Made Easy, application brief, Texas Instruments Literature Number SLMA004.
- PowerPAD Thermally Enhanced Package, technical brief, Texas Instruments Literature Number SLMA002.
- Karki, James. Fully Differential Amplifiers.application report, Texas Instruments Literature Number SLOA054D.
- Karki, James. Fully Differential Amplifiers Applications: Line Termination, Driving High-Speed ADCs, and Differential Transmission Lines. Texas Instruments Analog Applications Journal, February 2001.
- Carter, Bruce. A Differential Op-Amp Circuit Collection. application report, Texas Instruments Literature Number SLOA064.
- Carter, Bruce. Differential Op-Amp Single-Supply Design Technique, application report, Texas Instruments Literature Number SLOA072.
- Karki, James. Designing for Low Distortion with High-Speed Op Amps. Texas Instruments Analog Applications Journal, July 2001.



#### **REVISION HISTORY**

C	hanges from Revision D (January 2004) to Revision E	Page
•	Added WARNING to DESCRIPTION	1
•	Added Maximum junction temperature to prevent oscillation, T <sub>J</sub> and footnote to ABSOLUTE MAXIMUM RATINGS	3
•	Deleted power rating and footnote from PACKAGE DISSIPATION RATINGS	3
•	Added MAXIMUM DIE TEMPERATURE TO PREVENT OSCILLATION section	21

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2-Nov-2023

#### **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
THS4502CD	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	4502C	Samples
THS4502CDG4	ACTIVE	SOIC	D	8	75	TBD	Call TI	Call TI	0 to 70		Samples
THS4502CDGN	ACTIVE	HVSSOP	DGN	8	80	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	BCG	Samples
THS4502CDGNR	ACTIVE	HVSSOP	DGN	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	BCG	Samples
THS4502ID	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	45021	Samples
THS4502IDGK	ACTIVE	VSSOP	DGK	8	80	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ASX	Samples
THS4502IDGN	ACTIVE	HVSSOP	DGN	8	80	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BCI	Samples
THS4502IDGNR	ACTIVE	HVSSOP	DGN	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BCI	Samples
THS4502IDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	45021	Samples
THS4503CD	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	4503C	Samples
THS4503CDG4	ACTIVE	SOIC	D	8	75	TBD	Call TI	Call TI	0 to 70		Samples
THS4503CDGK	ACTIVE	VSSOP	DGK	8	80	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	ATY	Samples
THS4503CDGN	ACTIVE	HVSSOP	DGN	8	80	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	вск	Samples
THS4503CDGNR	ACTIVE	HVSSOP	DGN	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	вск	Samples
THS4503ID	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	45031	Samples
THS4503IDGK	ACTIVE	VSSOP	DGK	8	80	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ASY	Samples
THS4503IDGN	ACTIVE	HVSSOP	DGN	8	80	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BCL	Samples
THS4503IDGNR	ACTIVE	HVSSOP	DGN	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BCL	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

# PACKAGE OPTION ADDENDUM

www.ti.com 2-Nov-2023

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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#### OTHER QUALIFIED VERSIONS OF THS4503:

■ Enhanced Product : THS4503-EP

NOTE: Qualified Version Definitions:

• Enhanced Product - Supports Defense, Aerospace and Medical Applications

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 5-Dec-2023

# TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
THS4502CDGNR	HVSSOP	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
THS4502IDGNR	HVSSOP	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
THS4502IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
THS4503CDGNR	HVSSOP	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
THS4503IDGNR	HVSSOP	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1



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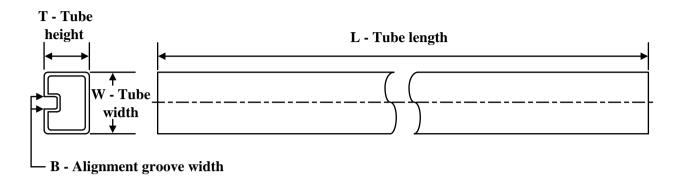
#### \*All dimensions are nominal

7 til dilliciololio ale Homiliai							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
THS4502CDGNR	HVSSOP	DGN	8	2500	358.0	335.0	35.0
THS4502IDGNR	HVSSOP	DGN	8	2500	358.0	335.0	35.0
THS4502IDR	SOIC	D	8	2500	350.0	350.0	43.0
THS4503CDGNR	HVSSOP	DGN	8	2500	358.0	335.0	35.0
THS4503IDGNR	HVSSOP	DGN	8	2500	358.0	335.0	35.0

# **PACKAGE MATERIALS INFORMATION**

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# **TUBE**



\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
THS4502CD	D	SOIC	8	75	505.46	6.76	3810	4
THS4502ID	D	SOIC	8	75	505.46	6.76	3810	4
THS4503CD	D	SOIC	8	75	505.46	6.76	3810	4
THS4503ID	D	SOIC	8	75	505.46	6.76	3810	4





## NOTES:

PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187.





- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.





- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.



3 x 3, 0.65 mm pitch

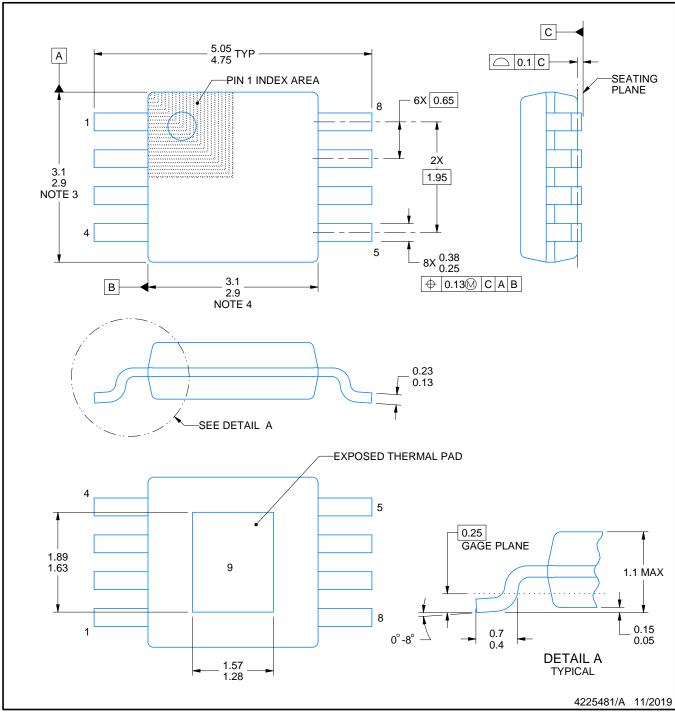
SMALL OUTLINE PACKAGE

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



# $\textbf{PowerPAD}^{^{\text{\tiny{TM}}}}\,\textbf{VSSOP - 1.1 mm max height}$

SMALL OUTLINE PACKAGE



## NOTES:

PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187.





- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.





- 10. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 11. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE INTEGRATED CIRCUIT



# NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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